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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/577,938	05/03/2006	Timothy J. Phillips	1241158	5737
23117 NIXON & VAN	7590 03/13/200 JDERHVE PC	7	EXAMINER	
901 NORTH GI	LEBE ROAD, 11TH F	LOOR	GHAZZAWI, M	OHAMMAD A
ARLINGTON, VA 22203			ART UNIT	PAPER NUMBER
			2814	
SHORTENED STATUTORY	Y PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE	
3 MON	NTHS	03/13/2007	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

		Application No.	Applicant(s)	
Office Action Summary		10/577,938	PHILLIPS ET AL.	
		Examiner	Art Unit	
		Mohammad Ghazzawi	2112	
Ti Period for R	he MAILING DATE of this communication ap	pears on the cover sheet with the c	orrespondence address	
A SHOR' WHICHE - Extensions after SIX (- If NO period - Failure to Any reply	TENED STATUTORY PERIOD FOR REPL VER IS LONGER, FROM THE MAILING D s of time may be available under the provisions of 37 CFR 1. 6) MONTHS from the mailing date of this communication. od for reply is specified above, the maximum statutory period reply within the set or extended period for reply will, by statute received by the Office later than three months after the mailin tent term adjustment. See 37 CFR 1.704(b).	NATE OF THIS COMMUNICATION 136(a). In no event, however, may a reply be timwill apply and will expire SIX (6) MONTHS from e, cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).	
Status				
2a)	sponsive to communication(s) filed on <u>03 N</u> is action is FINAL . 2b) This ce this application is in condition for allowalsed in accordance with the practice under	s action is non-final. Ince except for formal matters, pro		
Disposition	of Claims			
4a) 5)☐ Cla 6)☑ Cla 7)☑ Cla 8)☐ Cla	tim(s) <u>1-14</u> is/are pending in the application Of the above claim(s) is/are withdra tim(s) is/are allowed. tim(s) <u>1-8 and 10-14</u> is/are rejected. tim(s) <u>9</u> is/are objected to. tim(s) are subject to restriction and/o	wn from consideration.		
Application	Papers		ō	
10)⊠ The Apr Rer	e specification is objected to by the Examine drawing(s) filed on <u>03 May 2006</u> is/are: a) objection to the objection drawing sheet(s) including the correct oath or declaration is objected to by the Examine	D⊠ accepted or b) ☐ objected to be drawing(s) be held in abeyance. See tion is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).	
Priority unde	er 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.				
	References Cited (PTO-892)	4) Interview Summary		
2) Notice of I	Draftsperson's Patent Drawing Review (PTO-948) on Disclosure Statement(s) (PTO/SB/08) (s)/Mail Date 5-3-06.	Paper No(s)/Mail Da 5) Notice of Informal Pa 6) Other:	ite	

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DETAILED ACTION

Acknowledgment is made of Preliminary Amendment filed May 3, 2006.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1- 4 are rejected under 102(b) as being anticipated by Feng et al. (Feng) USPUB 2005/0054172.

Regarding claim 1, Feng discloses (page 5, para 0068) that the base layer of the transistor is highly doped for p-type.

Regarding claim 2, Feng discloses (page 8, para 0127) that asymmetry in well size provides improved directionality and speed of carrier transport.

Regarding claim 3 and 4, Feng discloses (page 7, para 0124) that other configurations and material systems can be used, including, as examples, GaAs and GaN based HBTs, or other direct bandgap material systems.

Claim 1, & 5-8 are rejected under 102(e) as being anticipated by Phillips USPUB 2005/0194613.

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Regarding claim 1, Phillips discloses (abstract) a field effect transistor having a primary channel that is preferably a low bandgap material. This means that the transistor includes at least one narrow bandgap region.

Regarding claims 5 & 6, Phillips discloses (abstract) a field effect transistor (FET) having a quantum well. He states that the low bandgap material comprises InSb or InAs.

Regarding claim 7, Phillips discloses (page 2, lines 1-5) that preferably the modulus of the difference between the impact ionization threshold IIT and the effective conduction band offset ΔEc (effective) between the primary and secondary channels being no more than 0.5 Eg (effective).

Regarding claim 8, Phillips discloses (page 4, lines 50-60) a quantum well field transistor wherein the quantum well is provided by a primary conduction channel and at least one secondary conduction channel immediately adjacent and in contact with the primary channel, the secondary channel having an effective bandgap greater than the effective bandgap Eg (effective) of the primary channel, wherein the modulus of the difference between the effective impact ionization threshold IIT (effective) and the effective conduction band offset ΔEc (effective) between the primary and secondary channels is not more than 0.4 eV.

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The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 10-11 and 13-14 are rejected under 103(a) as being unpatentable over Feng in view of Bakalski USPUB (2006/0261888).

Regarding claim 10, Feng does not explicitly disclose that the bipolar transistor is an npn bipolar transistor.

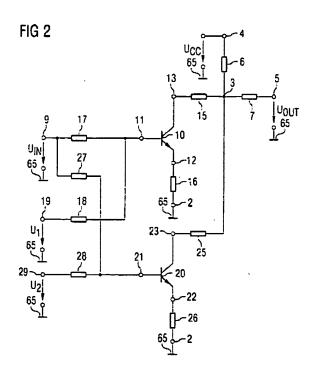
Bakalski discloses (page 6, para 0094) that the transistors are realized as npn bipolar transistors.

Bakalski is evidence that one of ordinary skill in the art would find a suggestion/motivation to modify Feng by using an npn bipolar transistor.

Therefore, it would have been obvious to modify Feng for advantages (page 6, para 0094) that npn transistors have great driver capability then pnp transistors.

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Regarding claims 13-14, Feng does not explicitly show complementary logic circuitry comprising a transistor.

Bakalski shows in Figure 2 complementary logic circuitry comprising a transistor.

Bakalski is evidence that one of ordinary skill in the art would find a suggestion/motivation to modify Feng by using complementary logic circuitry comprising a transistor.

Therefore, it would have been obvious to modify Feng for advantages of having an amplifier arrangement implementing the use of npn transistors.

Regarding claim 11, Feng discloses (page 3, para 0045) a transistor with a base region, a collector, an emitter, and a base contact. Feng discloses the claimed invention except for the narrow bandgap being greater than 0.5 eV. It would have been

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obvious to one of ordinary skill in the art at the time of the invention was made to modify Feng, since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or working ranges involves only routine skill in the art. In re Aller, 105 USPQ 233.

Claim 12 is rejected under 103(a) as being unpatentable over Phillips.

Phillips discloses the claimed invention except for the narrow bandgap being no more than 1.0 eV. It would have been obvious to one of ordinary skill in the art at the time of the invention was made to modify Phillips, since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or working ranges involves only routine skill in the art. In re Aller, 105 USPQ 233.

Allowable Subject Matter

Claim 9 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is an examiner's statement of reasons for allowance:

The prior arts of record do not anticipate or render obvious to one of ordinary skill in the art one junction which is bias able to reduce the intrinsic conduction in the quantum well and confine charge carriers predominantly to one type only corresponding to an extrinsic saturated regime.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably

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accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mohammad Ghazzawi whose telephone number is (571) 272-9756. The examiner can normally be reached on m-f every other friday off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tarifur Chowdhury can be reached on (571) 272-9819. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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